

ABSTRACT

MEMORY DEVICE

5 A memory device is provided. A memory device includes a
memory cell array having variable resistance memory cells that
are coupled to and disposed between first conductive lines
extending in a first direction and second conductive lines
crossing the first conductive lines, and a selection circuit
10 configured to select the first conductive lines. The second
conductive lines include straight conductive lines extending in a
second direction that crosses the first direction, and first
bending conductive lines spaced apart from the selection circuit
by the straight conductive lines, the first bending conductive
15 lines extending parallel with each other, and having an L shape.

FIG. 2